

N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

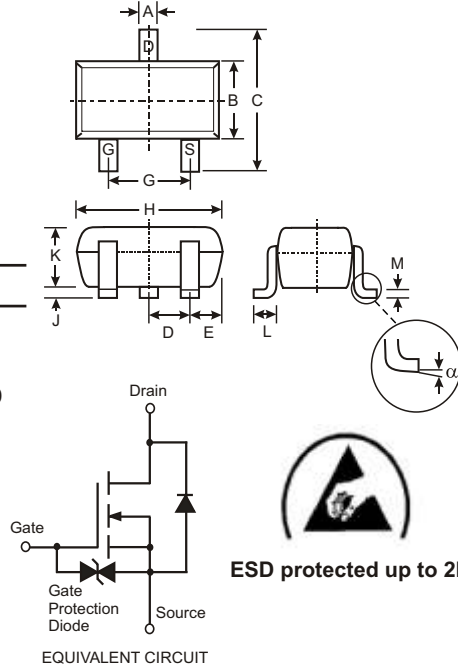
NEW PRODUCT

Features

- Low On-Resistance: $R_{DS(ON)}$
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected Up To 2kV**
- **"Green" Device (Note 4)**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: See Last Page
- Ordering & Date Code Information: See Last Page
- Weight: 0.006 grams (approximate)



SOT-323		
Dim	Min	Max
A	0.25	0.40
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
E	0.30	0.40
G	1.20	1.40
H	1.80	2.20
J	0.0	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.18
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

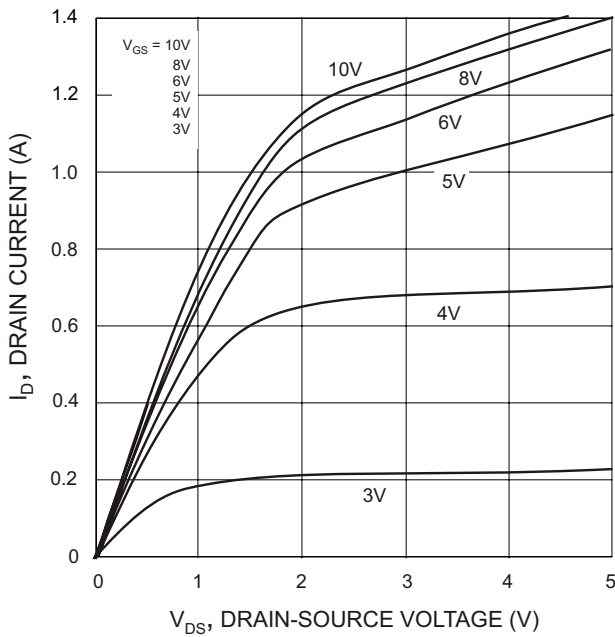
Characteristic	Symbol	Value	Units
Drain-Source Voltage	V_{DSS}	60	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current (Note 1)	I_D	300	mA
		800	
Total Power Dissipation (Note 1)	P_d	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	625	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150	$^\circ\text{C}$

- Note:
1. Device mounted on FR-4 PCB.
 2. No purposefully added lead.
 3. Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$.
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

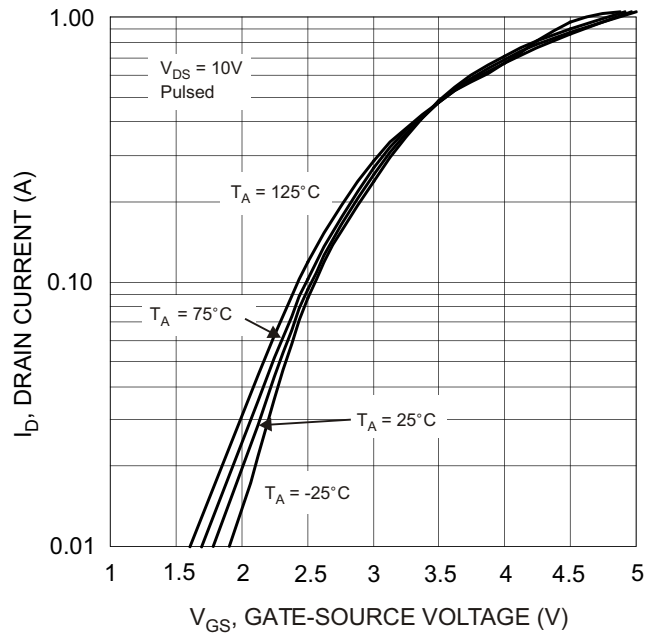
Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	$V_{DS} = 10V, I_D = 1mA$
Static Drain-Source On-Resistance	$R_{DS(on)}$	—	—	2.0	Ω	$V_{GS} = 10V, I_D = 0.5A$
				3.0		$V_{GS} = 4.5V, I_D = 0.2A$
Forward Transfer Admittance	$ Y_{fs} $	80	—	—	ms	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	5.0	pF	

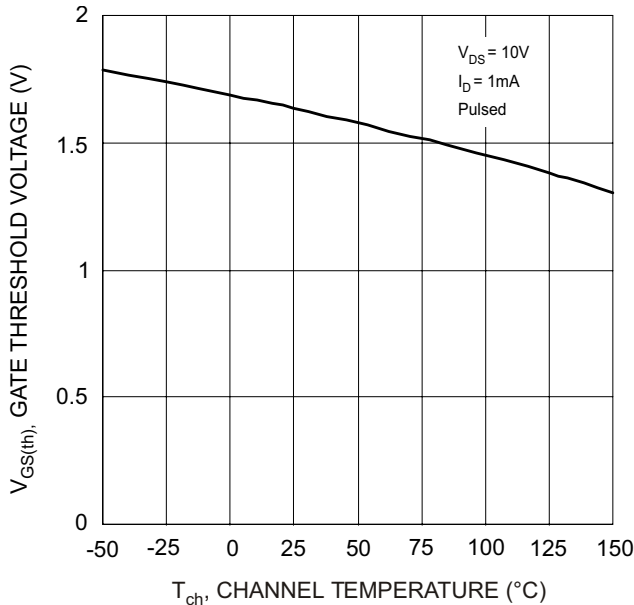
Notes: 5. Short duration test pulse used to minimize self-heating effect.



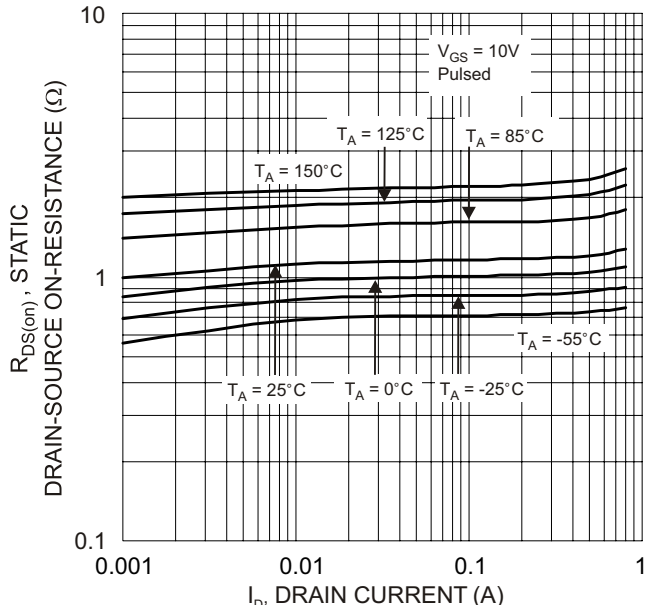
V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Fig. 1 Typical Output Characteristics



V_{GS} , GATE-SOURCE VOLTAGE (V)
Fig. 2 Typical Transfer Characteristics



T_{ch} , CHANNEL TEMPERATURE ($^\circ\text{C}$)
Fig. 3 Gate Threshold Voltage vs. Channel Temperature



I_D , DRAIN CURRENT (A)
Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

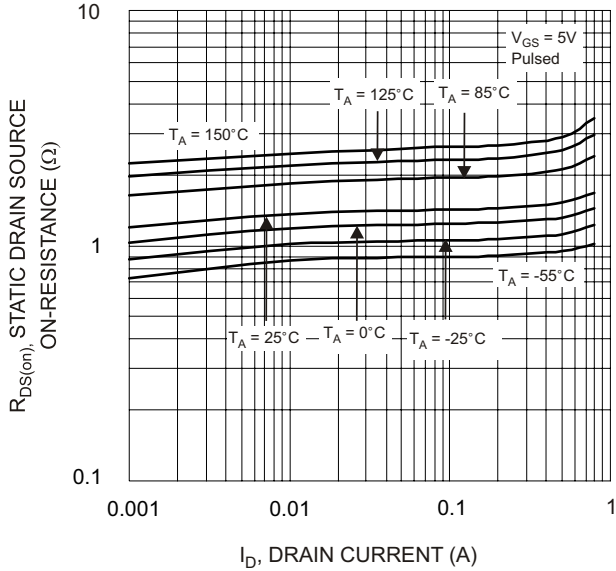


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

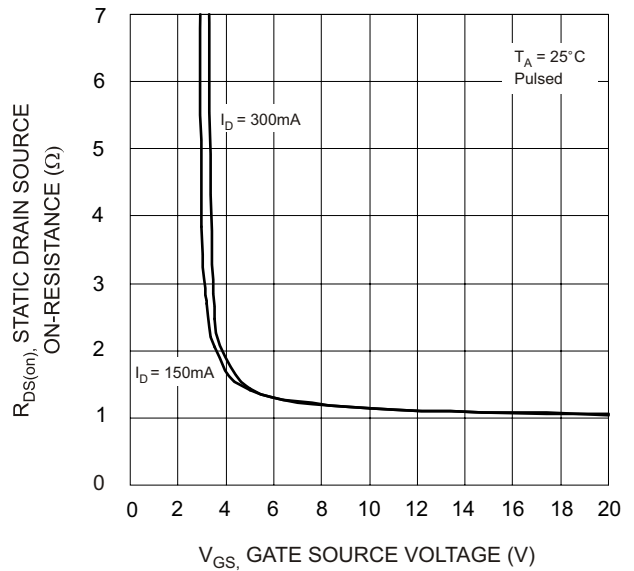


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

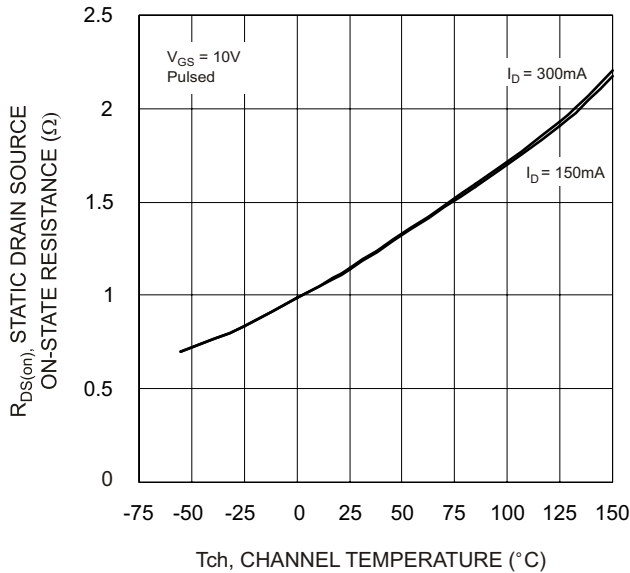


Fig. 7 Static Drain-Source On-State Resistance vs. Channel Temperature

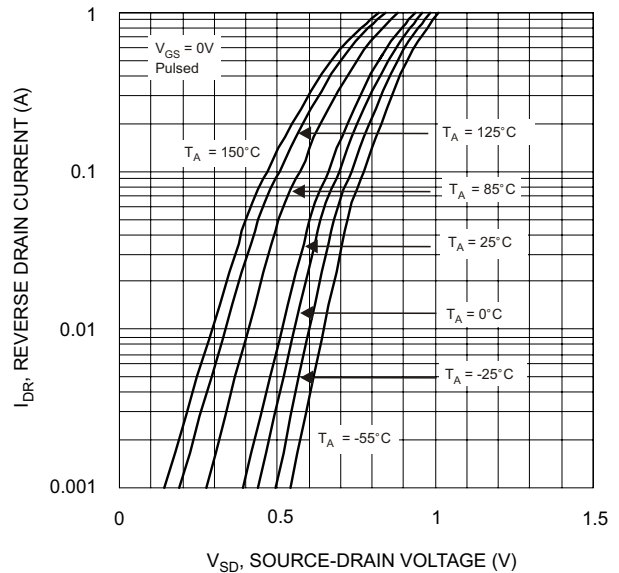


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

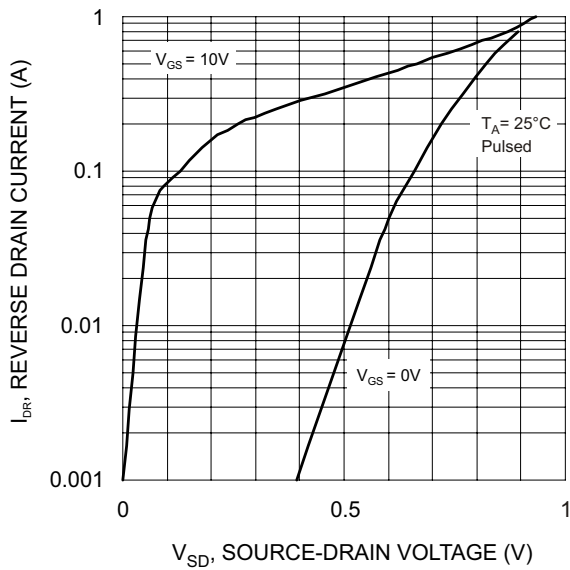


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

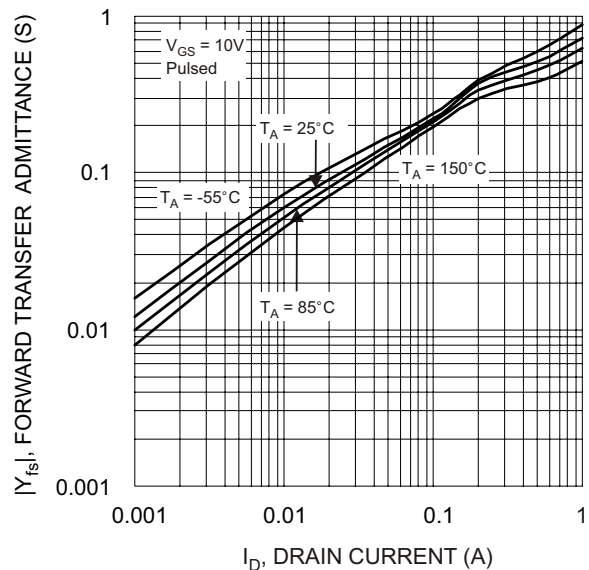


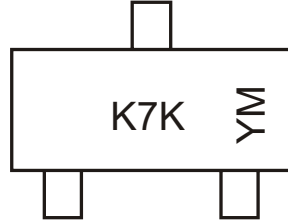
Fig. 10 Forward Transfer Admittance vs. Drain Current

Ordering Information (Note 6)

Device	Packaging	Shipping
DMN601WK-7	SOT-323	3000/Tape & Reel

Notes: 6. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K7K = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: S = 2005
 M = Month ex: 9 = September

Date Code Key

Year	2005	2006	2007	2008	2009
Code	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D